WSTBSS138

N-Ch MOSFET

General Description

The WSTBSS138 is the highest performance trench N-ch MOSFETs with extreme high cell density , which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The WSTBSS138 meet the RoHS and Green Product requirement , 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

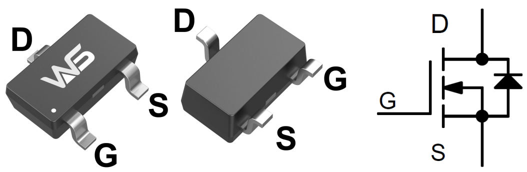
Product Summery

BVDSS	RDSON	ID
60V	110mΩ	2.1A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

SOT-23-3L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ 10V[1]	2.1	A
I_D@T_C=70℃	Continuous Drain Current, V_{GS} @ 10V[1]	1.5	A
I_{DM}	Pulsed Drain Current[2]	10	A
EAS	Single Pulse Avalanche Energy[3]	15	mJ
I_{AS}	Avalanche Current	21	A
P_D@T_A=25℃	Total Power Dissipation[4]	1.25	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient [1]	---	125	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	---	25	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	55	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BVDSS Temperature Coefficient	Reference to 25℃ , I_D=1mA	---	0.041	---	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=4.5V , I_D=2.1A	---	85	110	mΩ
		V_{GS}=2.5V , I_D=1.5A	---	95	120	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1.0	1.5	2.5	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-4.7	---	mV/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=44V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=44V , V_{GS}=0V , T_J=85℃	---	---	5	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=5V , I_D=4A	---	10	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	2.5	5	Ω
Q_g	Total Gate Charge (10V)	V_{DS}=27V , V_{GS}=4.5V , I_D=2.1A	---	2.1	3.9	nC
Q_{gs}	Gate-Source Charge		---	0.6	---	
Q_{gd}	Gate-Drain Charge		---	0.8	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=27V , V_{GS}=10V , R_G=6Ω I_D=1A	---	3.6	---	ns
T_r	Rise Time		---	3.5	---	
$T_{d(off)}$	Turn-Off Delay Time		---	32	---	
T_f	Fall Time		---	3	---	
C_{iss}	Input Capacitance	V_{DS}=15V , V_{GS}=0V , f=1MHz	---	295	---	pF
C_{oss}	Output Capacitance		---	40	---	
C_{rss}	Reverse Transfer Capacitance		---	15	---	

Guaranteed Avalanche Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
EAS	Single Pulse Avalanche Energy[5]	V_{DD}=25V , L=0.1mH , I_{AS}=15A	15.2	---	---	mJ

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current[1,6]	V_G=V_D=0V , Force Current	---	---	1	A
I_{SM}	Pulsed Source Current[2,6]		---	---	4	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=1A , T_J=25℃	---	---	1.2	V
t_{rr}	Reverse Recovery Time	I_F=4A , dI/dt=100A/μs , T_J=25℃	---	10.1	---	nS
Q_{rr}	Reverse Recovery Charge		---	6.4	---	nC

Note :
1.The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper,t<10sec.
2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%
3.The EAS data shows Max. rating . The test condition is V_{DD}=25V,V_{GS}=10V,L=0.1mH,I_{AS}=15A
4.The power dissipation is limited by 150℃ junction temperature
5.The Min. value is 100% EAS tested guarantee.
6.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

TYPICAL CHARACTERISTICS (25℃ Unless Note)

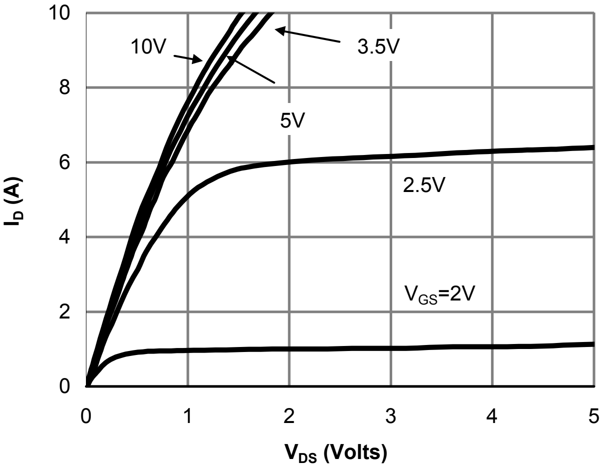


Fig 1: On-Region characteristics

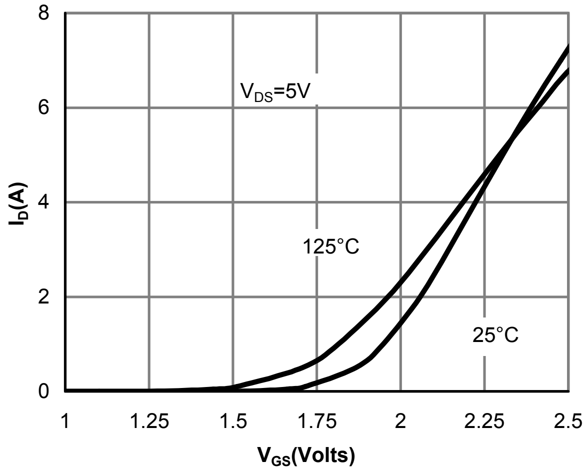


Figure 2: Transfer Characteristics

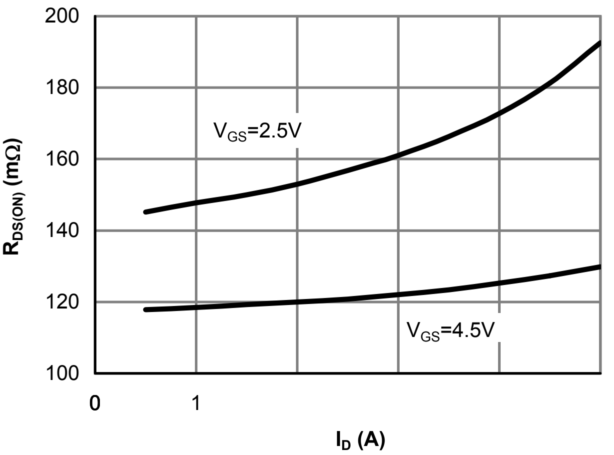


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

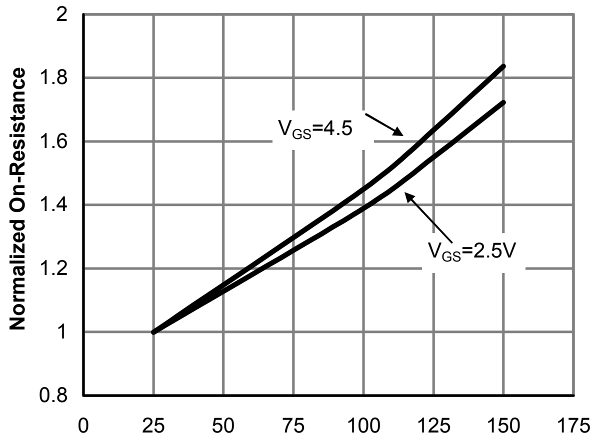


Figure 4: On-Resistance vs. Junction Temperature

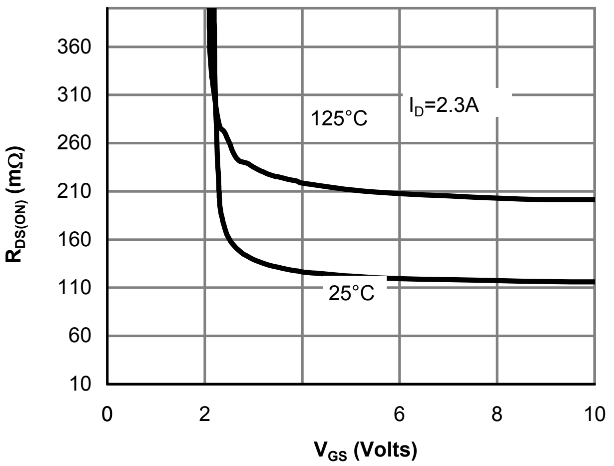


Figure 5: On-Resistance vs. Gate-Source Voltage

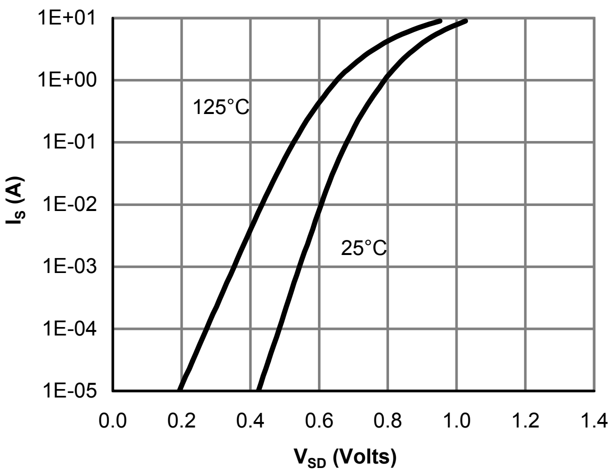


Figure 6: Body-Diode Characteristics

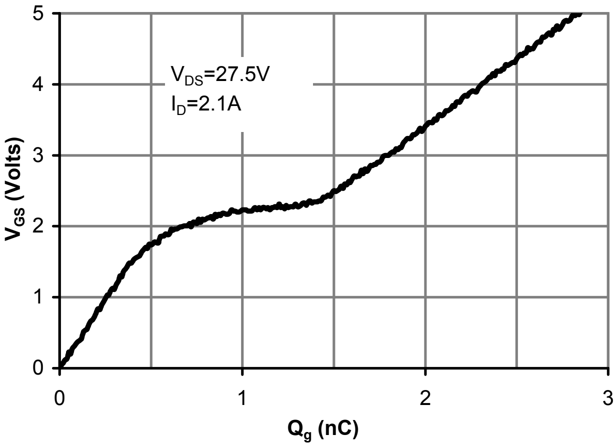


Figure 7: Gate-Charge Characteristics

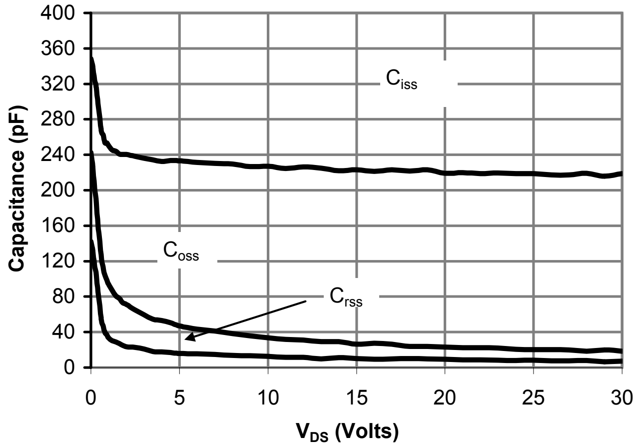


Figure 8: Capacitance Characteristics

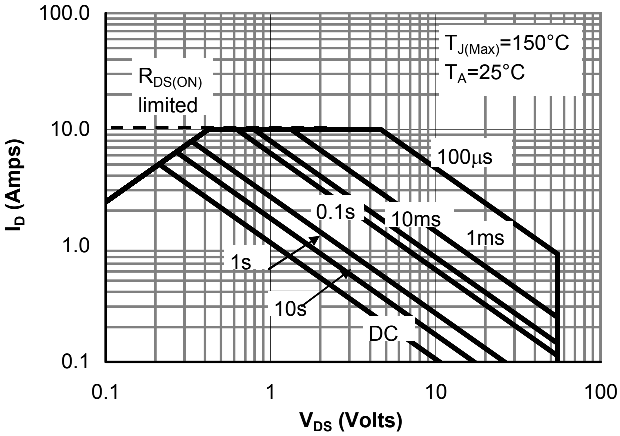


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

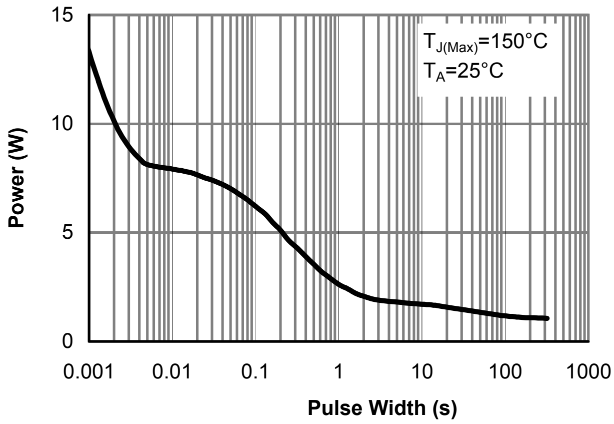


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

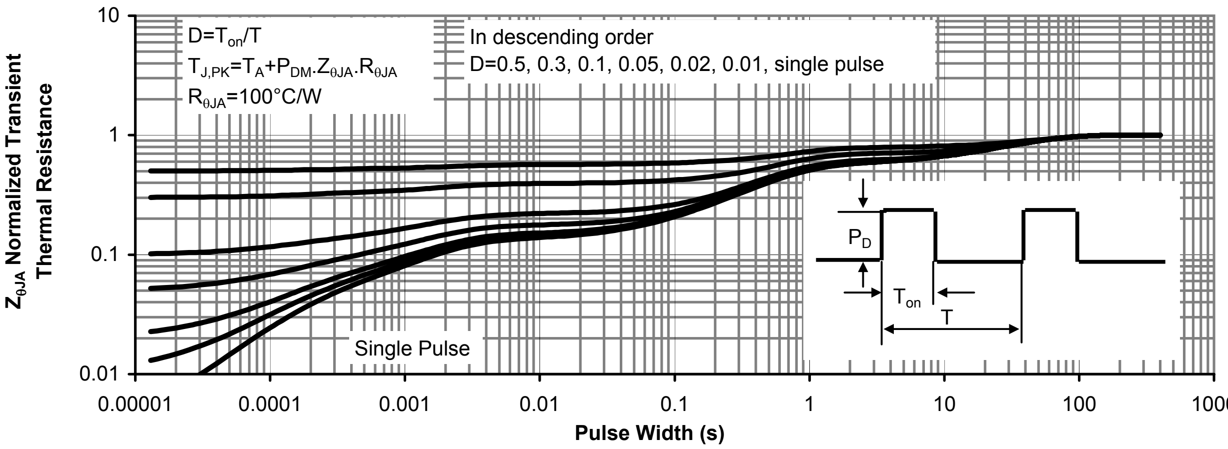


Figure 11: Normalized Maximum Transient Thermal Impedance

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